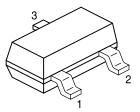


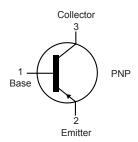


- For general AF applications
- High current gain
- · Low collector-emitter saturation voltage
- Complementary types: BCW65,BCW66(NPN)

Applications:

 This device is designed for general purpose amplifier and switching applications





Pin Configuration:

- 1. Base
- 2. Emitter
- 3. Collector

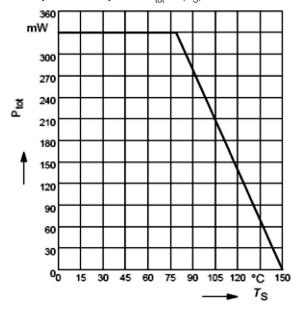
Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector - Base Voltage	V _{CBO}	-60	60	
Collector - Emitter Voltage	V _{CEO}	-45	V	
Emitter - Base Voltage	V _{ebo}	-5		
DC Collector Current	I _C	-1	А	
Collector Current Continuous	I _C	-800	mA	
Total Device Dissipation	P_{D}	330	mW	
Junction Thermal Resistance	R _{thJS}	215	°C/W	
Junction and Storage Temperature	T _j , T _{stg}	-65 to +150	°C	

Electrical Characteristics ($T_a = 25$ °C unless otherwise noted)

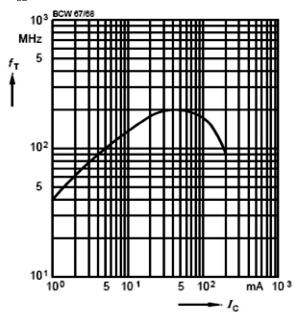
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Collector - Base Breakdown Voltage	V _{(BR)CBO}	I _C =-10μΑ, I _E =0	-60				
Collector - Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-45			V	
Emitter - Base Breakdown Voltage	V _{(BR)EBO}	I _E =-10μΑ, I _C =0	-5				
Collector Cut-Off Current	I _{CBO}	V_{CB} =-45V, I_{E} =0			-20	nA	
Emitter Cut-Off Current	I _{EBO}	V_{EB} =-4V, I_{C} =0			-20		
DC Current Gain	h _{FE}	V _{CE} =-10V, I _C =-0.1mA	50 80				
		V _{CE} =-1V, I _C =-10mA	120 180				
		V _{CE} =-1V, I _C =-100mA	160 250	250 350	400 630		
		V _{CE} =-2V, I _C =-500mA	60 100				
Collector - Emitter Saturation Voltage	V _{CE(sat)}	I _C =-100mA, I _B =-10mA I _C =-500mA, I _B =-50mA			-0.3 -0.7	V	
Base Emitter Saturation Voltage	V _{BE(sat)}	I _C =-100mA, I _B =-10mA I _C =-500mA, I _B =-50mA			-1.25 -2	v	
Transition Frequency	f_T	V _{CE} =-5V, I _C =-50mA f=20MHz		200		MHz	

Total power dissipation $P_{\text{tot}} = f(T_{\text{S}})$



Transition frequency $f_{\rm T}$ = $f(I_{\rm C})$

$$V_{\rm CE} = 5 \rm V$$

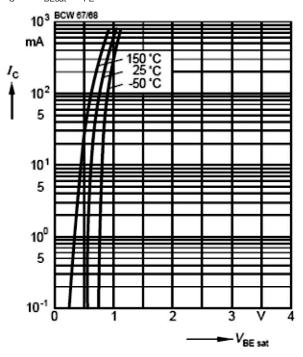


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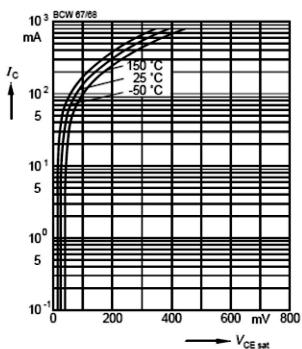
Base-emitter saturation voltage

 $I_{\rm C} = f(V_{\rm BEsat}), h_{\rm FE} = 10$



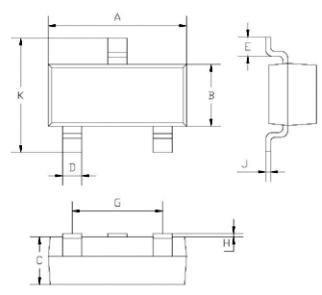
Collector-emitter saturation voltage

$$I_{C} = f(V_{CEsat}), h_{FE} = 10$$



Package Outline

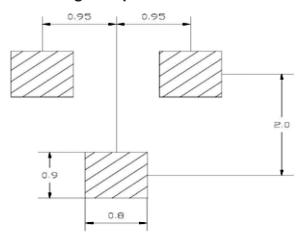
Plastic surface mounted package



Dimensions	Min. Max.		
А	2.85	2.95	
В	1.25	1.35	
С	1 Typical		
D	0.4 Typical		
E	0.35	0.48	
G	1.85	1.95	
Н	0.02	0.1	
J	0.1 Typical		
K	2.35	2.45	

Dimensions: Millimetres

Soldering Footprint



Dimensions: Millimetres

Part Number Table

Description	Part Number		
Transistor, PNP, 0.8A, 45V, SOT23	BCW68G		
	BCW68H		

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